

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(semiconductor and plurality and wiring and laminat\$3 and insulat\$3 and electrode and via and terminal and strip and shape and parallel and longitudinal and direction and distance and adjacent and capacitor).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 13:06
L2	1	(semiconductor and plurality and wiring and laminat\$3 and insulat\$3 and electrode and via and capacitor and integrated and circuit and diameter).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 13:07
L3	0	(semiconductor and plurality and wiring and laminat\$3 and insulat\$3 and electrode and via and capacitor and terminal and upper and lower and another).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 13:08
L4	0	(semiconductor and plurality and wiring and laminat\$3 and insulat\$3 and electrode and via and capacitor and terminal and (n adj type) and (p adj type) and potential and another and high\$3 and low\$3).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/15 13:09